

ZXTP05120HFF 120V, SOT23F, PNP medium power Darlington transistor

Summary

BV_{CEO} > -120V I_{C(cont)} = -1A V_{CE(sat)} < 1.1V @ 1A P_D = 1.5W

Complementary part number ZXTN04120HFF

Description

This high performance PNP Darlington transistor is housed in the small outline SOT23 flat package for applications where space is at a premium.

Features

- Darlington transistor
- 120 volt
- 1 amp continuous rating
- Small outline surface mount SOT23 flat package

Applications

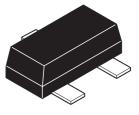
• High side drivers

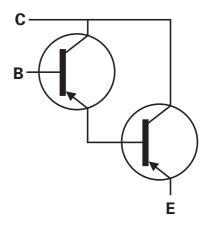
Ordering information

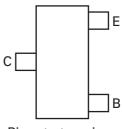
DEVICE Reel size		Tape width	Quantity	
(inches)		(mm)	per reel	
ZXTP05120HFFTA	7	8	3000	

Device marking

1F7







Pinout - top view

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V _{CBO}	-140	V
Collector-emitter voltage	V _{CEO}	-120	V
Emitter-base voltage	V _{EBO}	-10	V
Continuous collector current (c)	Ι _C	-1	А
Peak pulse current	I _{CM}	-4	А
Base current	Ι _Β	-0.5	А
Power dissipation @ $T_{amb} = 25^{\circ}C^{(a)}$	P _D	0.84	W
Linear derating factor		6.72	mW/°C
Power dissipation @ $T_{amb} = 25^{\circ}C^{(b)}$	P _D	1.34	W
Linear derating factor		10.72	mW/°C
Power dissipation @ $T_{amb} = 25^{\circ}C^{(c)}$	P _D	1.50	W
Linear derating factor		12.0	mW/°C
Power dissipation @ $T_{amb} = 25^{\circ}C^{(d)}$	P _D	2.0	W
Linear derating factor	P _D	16.0	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to 150	°C

Thermal resistance

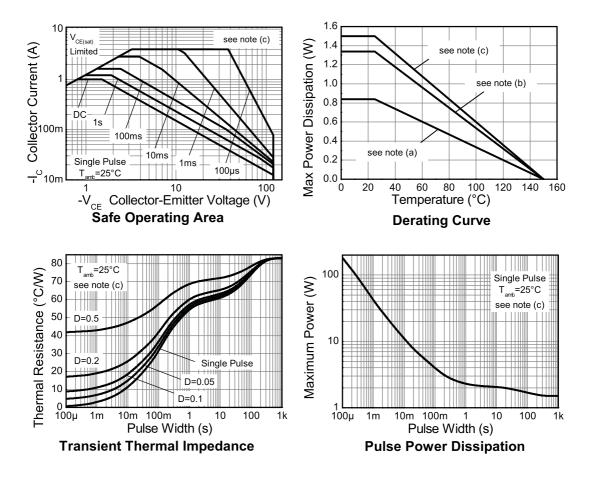
Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	149	°C/W
Junction to ambient ^(b)	$R_{\Theta JA}$	93	°C/W
Junction to ambient ^(c)	$R_{\Theta JA}$	83	°C/W
Junction to ambient ^(d)	$R_{\Theta JA}$	60	°C/W

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (d) As (c) above measured at t<5secs.

Characteristics



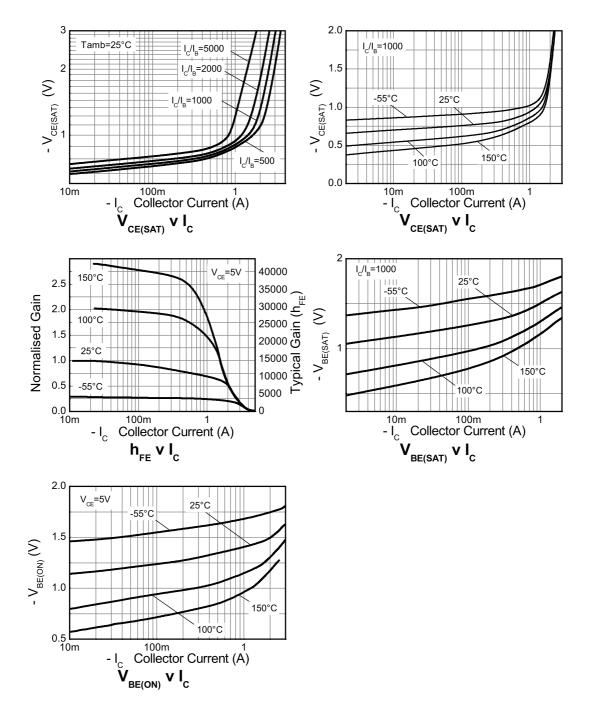
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	-140	-170		V	I _C = -100μA
Collector-emitter breakdown voltage (base open)	BV _{CEO}	-120	-140		V	I _C = -10mA ^(*)
Emitter-base breakdown voltage	BV _{EBO}	-10	-16		V	I _E = -100μA
Collector-base cut-off current	I _{CBO}		<-1	-100	nA	V _{CB} = -120V
				-10	μA	$V_{CB} = -120V, T_{amb} = 100^{\circ}C$
Collector-emitter cut-off current	I _{CES}		<-0.1	-10	μA	V _{CB} = -120V
Emitter-base cut-off current	I _{EBO}		<-1	-100	nA	V _{EB} = -8V
Collector-emitter saturation	V _{CE(sat)}		-0.77	-0.9	V	$I_{C} = 250 \text{mA}, I_{B} = 0.25 \text{mA}^{(*)}$
voltage			-0.9	-1.1	V	I _C = -1A, I _B = -1mA ^(*)
			-1.3	-2.0	V	$I_{C} = -2A, I_{B} = -2mA^{(*)}$
Base-emitter saturation voltage	V _{BE(sat)}		-1.5	-1.7	V	I _C = -1A, I _B = -1mA ^(*)
Base-emitter turn-on voltage	V _{BE(on)}		-1.4	-1.7	V	$I_{C} = -1A, V_{CE} = -5V^{(*)}$
Static forward current	h _{FE}	ЗK	14k			I _C = -50mA, V _{CE} = -5V ^(*)
transfer ratio		ЗK	11k			$I_{C} = -500 \text{mA}, V_{CE} = -5V^{(*)}$
		ЗК	10k	30K		$I_{C} = -1A, V_{CE} = -5V^{(*)}$
		2K	8k			$I_{C} = -2A, V_{CE} = -5V^{(*)}$
Transition frequency	f _T		150		MHz	I _C = -100mA, V _{CE} = -10V f = 20MHz
Output capacitance	C _{ibo}		67	90	pF	V _{EB} = -0.5V, f = 1MHz ^(*)
Output capacitance	C _{obo}		22	40	pF	V _{CB} = -10V, f = 1MHz ^(*)
Delay time	t _d		556		ns	V _{CC} = -10V.
Rise time	t _r		212		ns	$I_{\rm C} = -0.5 {\rm A},$
Storage time	t _s		681		ns	I _{B1} = I _{B2} = -0.5mA.
Fall time	t _f		304		ns	

Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

NOTES:

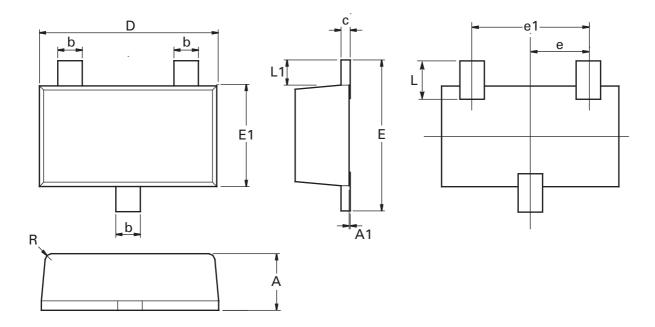
(*) Measured under pulsed conditions. Pulse width ${\leq}300\mu s;$ duty cycle ${\leq}2\%.$

Typical characteristics



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Package outline - SOT23F



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	0.80	1.00	0.0315	0.0394	E	2.30	2.50	0.0906	0.0984
A1	0.00	0.10	0.00	0.0043	E1	1.50	1.70	0.0590	0.0669
b	0.35	0.45	0.0153	0.0161	L	0.48	0.68	0.0189	0.0268
С	0.10	0.20	0.0043	0.0079	L1	0.30	0.50	0.0153	0.0161
D	2.80	3.00	0.1102	0.1181	R	0.05	0.15	0.0019	0.0059
е	0.95	ref	0.037	74 ref	0	0°	12°	0°	12°
e1	1.80	2.00	0.0709	0.0787	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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